

DEPOSITING A NUCLEATION LAYER OF TUNGSTEN SILICIDE (WSi_x) ON A SUBSTRATE USING A (CVD) PROCESS WITH SILANE (SiH_4) AS A SILICON SOURCE GAS.

DEPOSITING A TUNGSTEN SILICIDE (WSi_x) FILM ON THE NUCLEATION LAYER USING A (CVD) PROCESS WITH DICHLOROSILANE AS A SILICON SOURCE GAS.

Fig. 1

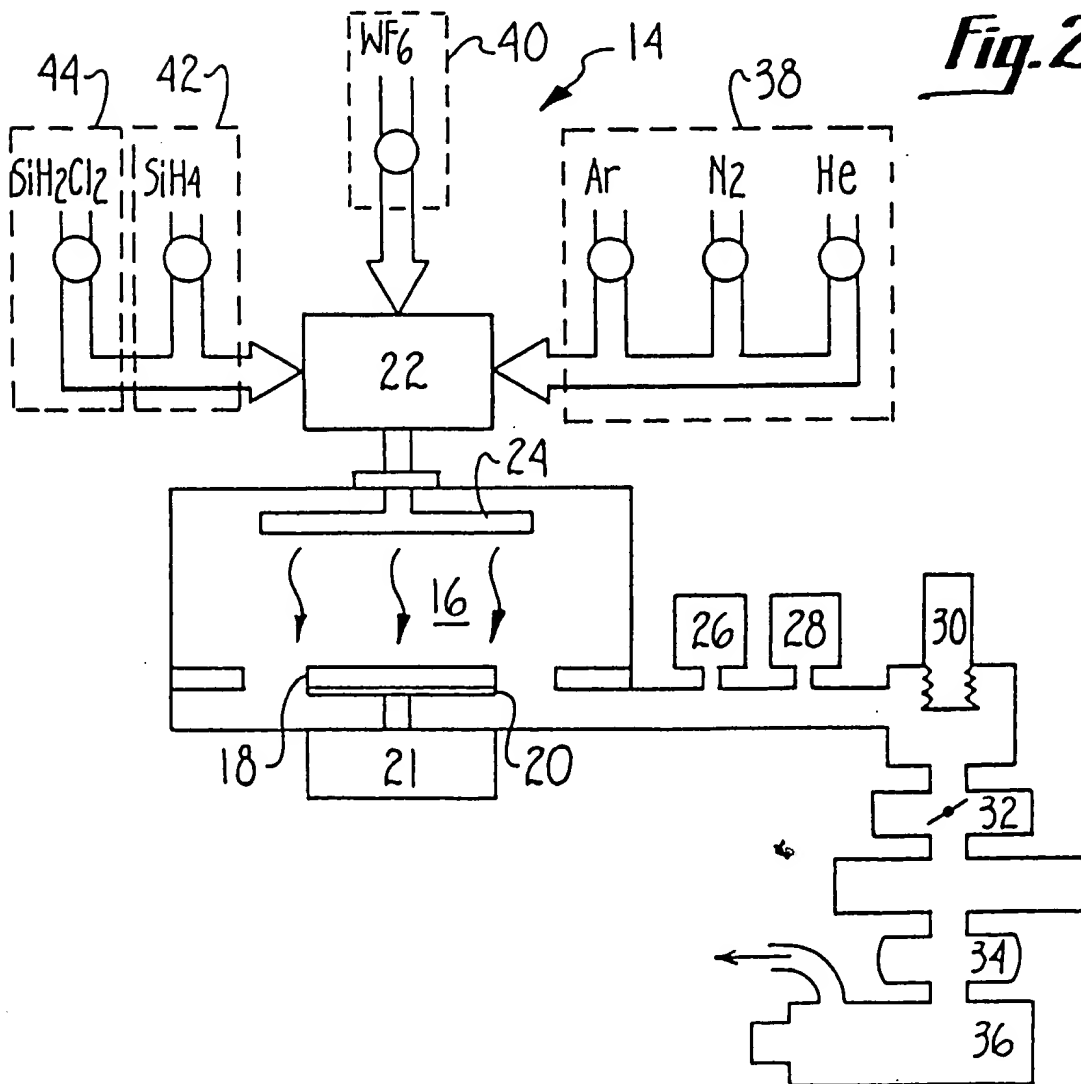


Fig. 2